

# How to unleash the power savings of GaN in high-power, high voltage applications

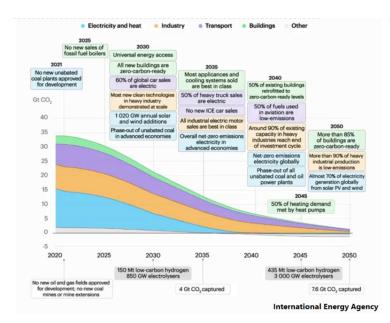
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2024

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### Electrification is essential: Motors are critical

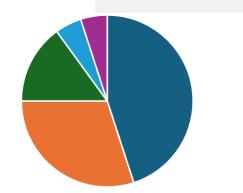
Inevitable move towards electrification: pressure from net zero.



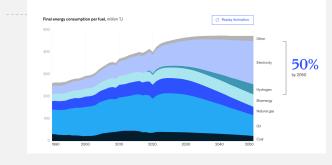
Electric motors are the worlds biggest energy consumers.

~50% of global electricity more than any other application.

Electric motor today are often shockingly inefficient: scope to reduce waste by 25%



Electric usage will triple by 2050 (83 ExaJ to 252ExaJ) >3x growth in motors



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*Electric motors are the largest single-energy use with half of global electricity consumption.* 

There is a huge, untapped potential for energy efficiency in motors: around 25% of electricity use could be saved cost-effectively, which would reduce global electricity demand by 10%.

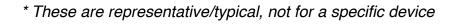
However, the energy efficiency of motors has been neglected in comparison with other sustainable energy opportunities

- IEA



### GaN has great advantages over SiC or Si

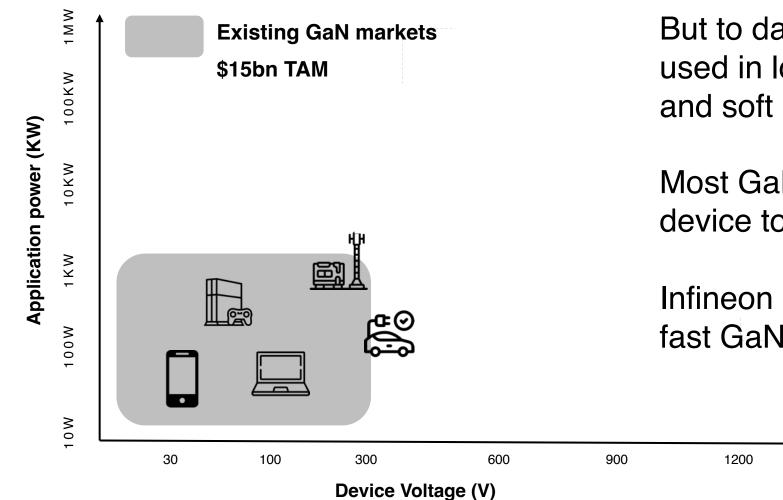
- Lower gate capacitance: GaN <1 nC-Ω vs 4 nC-Ω for Si\*</li>
- Lower output capacitance
- GaN output charge <5 nC- $\Omega$  vs Si at 25 nC- $\Omega^*$
- Zero reverse recovery / no body diode No reverse recovery losses Typical SiC FET >85 nC of reverse-recovery charge\*
- Lower switching energy: half that of SiC
- Faster switching speed: up to 10MHz
- Lower cost: Si substrate, 300m wafer



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1 MW IGBT 100 kW SiC Power 10 kW 1 kW GaN 100 W MOSFET 1 kHz 10 kHz 100 kHz 1 MHz 10 MHz Frequency

### If only GaN could do higher power...



But to date GaN has only been used in lower power applications and soft switching

Most GaN vendors "sandbag" the device to make it "look like" Si

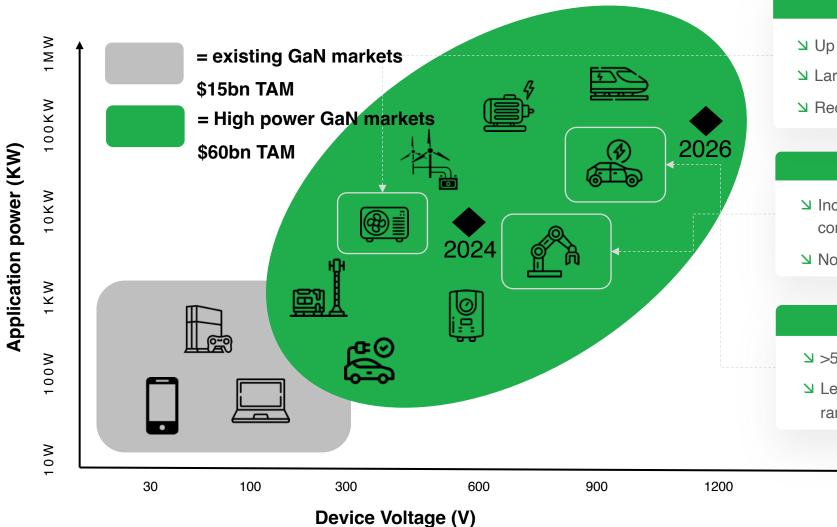
Infineon one of few vendors with fast GaN at high power



### ... but it can!

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#### HVAC

- ↘ Up to 20% efficiency improvement
- ❑ Large energy saving for consumers

#### Industrial

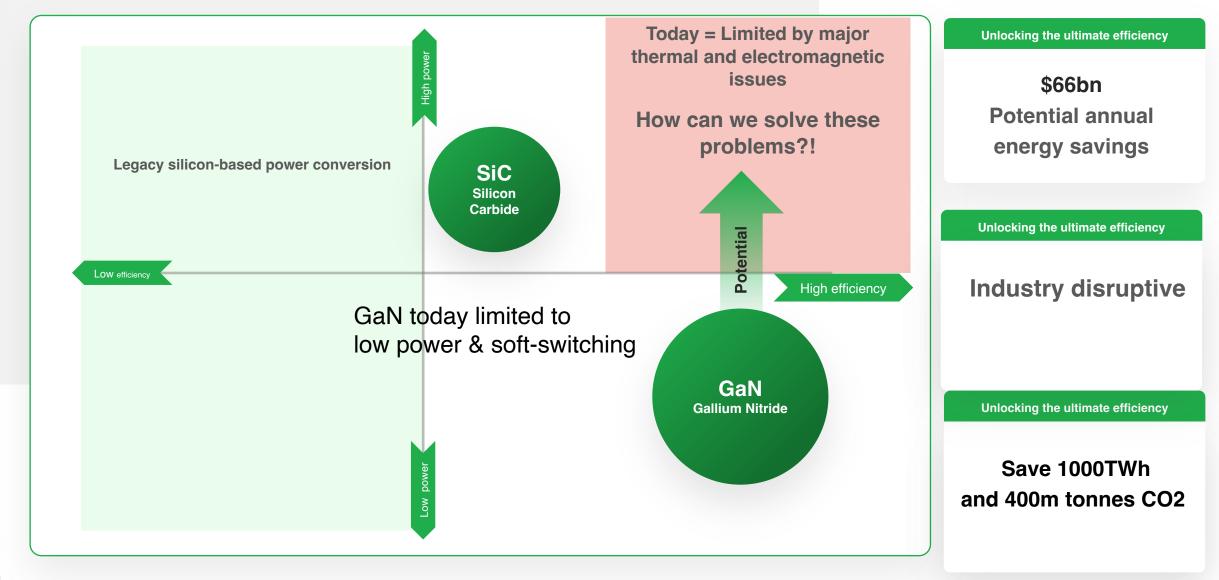
- Increased power density to reduce cabling complexities
- ↘ No need for screened cables

#### **Electric Vehicles**

- > >5% efficiency improvement over SiC
- Less heat, reduce weight to further increase range



### GaN can replace IGBT & SiC: Higher power at higher efficiency



### The problem: Why efficient motor drives are critical

- Many motors today are shockingly inefficient. Only 23% use a Variable Frequency Drive (VFD) to control speed, but even those are inefficient
- The faster the transistors in the VFDs can switch, the more energy is saved. Running VFDs at higher frequencies increases power density (reducing size and weight)
- GaN has great advantages over Si IGBT or SiC
- But to completely replace them, new system design is required
- The worlds of power engineering and RF / microwave engineering have collided: the old approaches no longer work



### To use GaN = RF Meets Power

### POWER

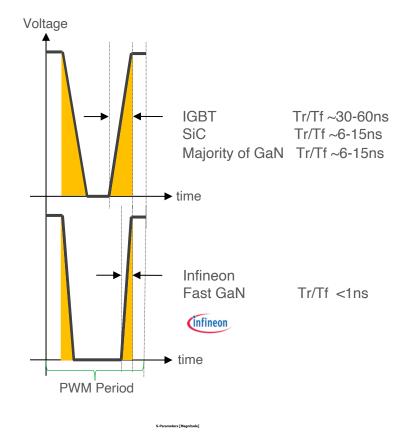
High power = kW 10s-100s of Amps Low frequency = kHz RF

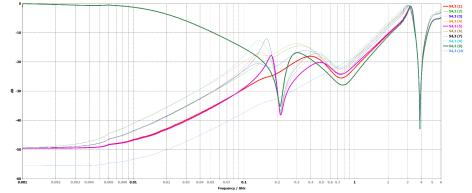
Low power = mW Different units: dBm, Ohms High frequency = MHz, GHz

The future of Power Electronics: Switching 10s-100s of Amps at MHz Combining kW with GHz

### The problem with hard switching...

- Switching the DC bus directly: no ZVS and/or ZCS advantage
- Only way to reduce wasted energy in transitions is by transitioning faster (less time in resistive region = less energy wasted)
- But when we do this, we have a microwave RF power system:
  - Any power path longer than ¼ wave is a transmission line and needs to be terminated or we get highly destructive reflections!
  - ¼ wave in power systems IGBT switching systems is around 1.5m not really an issue in a motor drive!
  - ¼ wave in a fast GaN system is around 5cm (harmonics at 1-2cm): starts to get interesting...
- Most GaN transistors are "sandbagged" GaN Systems/Infineon are unusual in supporting high power (650V, 15A) at high frequencies (<1ns switching)</li>

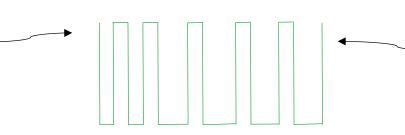




### The Benefits and Challenges of Fast Switching

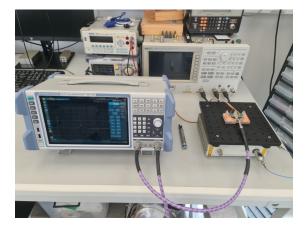
#### **PWM frequency of 1MHz**

Makes sinus filter very much smaller, lighter, cheaper



#### **Benefits**

- Sinus filter is is built into the architecture reduced from 36kg to 100g
- All reactive components (L's and C's) are reduced in size (and cost!) by ~100x
- GaN has no body diode: less wasted energy



RF output impedance of modules being characterised in our lab.

#### <1ns rise/fall time

Very little time in resistive region = very low losses, less waste heat But RF challenges: signals into GHz

#### Challenges

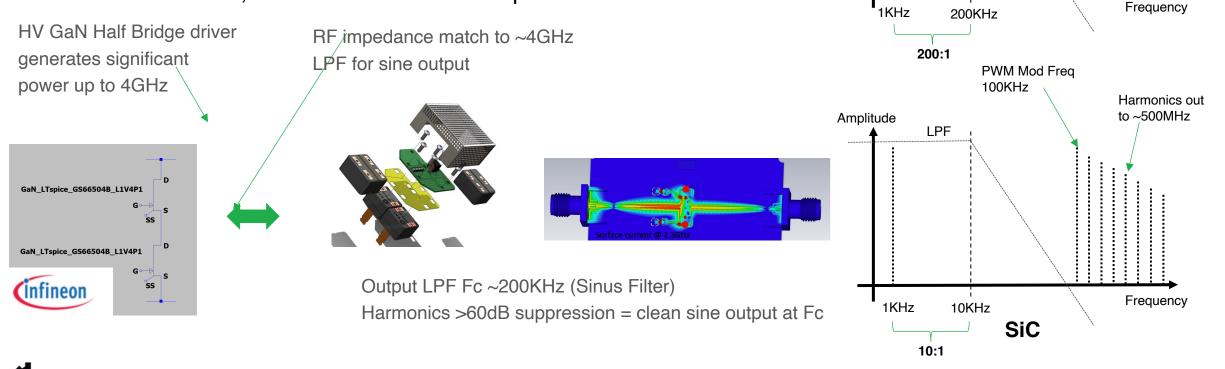
- Complex output impedance of GaN H-Bridge must be terminated
- LC output filter must have a self resonant frequency of several GHz to avoid EMC issues
- Conducted and radiated emissions must be managed



### Filtering

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- Higher PWM frequency makes filtering easier: greater separation between motor drive, PWM & harmonics
- High energy and fast rise/fall makes filtering essential otherwise dV/dt would be unacceptable
- Clean sine (very low THD) has major benefits for motor: less heat, lower eddy currents, less winding stress, less noise/vibration, no common mode or dc path



**Fast GaN** 

PWM Mod Freq 1-2MHz

Harmonics out

to ~4GHz

Motor drive 50-1000Hz

LPF

Amplitude

Low order filter

### This is real...

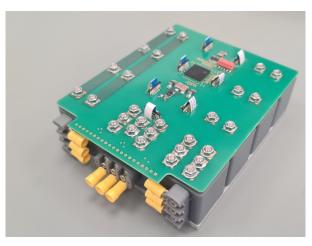


### 400V (230V 3phase) 7.5kW GaN-based VFD

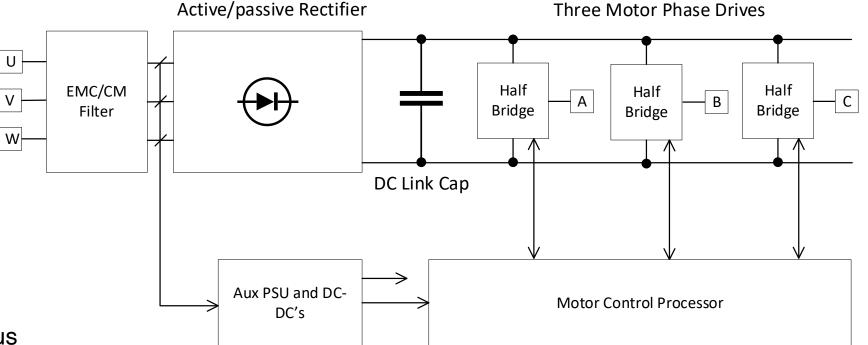
- Ultra-high efficiency, ultra-compact
- 1MHz internal switching PWM (<1ns switching time)
- Compact integrated sinus filter (no high dV/dt, no dc component)
- 0-500Hz output (0-30,000rpm), pure sine (~0% THD)
- Active rectifier: <5% THD, no electrolytic caps, high MTBF
- GaN transistors: low losses, minimal heat dissipation
- Volume: 1litre (15cm x 16cm x 4cm)



### **Complete VFD Module (with integrated filter)**



- 15cm x 15cm x 4cm
- 11 volume
- 3x Half bridge, rectifier, sinus filter, control processor





### Traction

## ABB

Winner Open Innovation competition: Contract to develop next-generation GaN-based VFD for the world's largest supplier of industrial electric motors

"QPT's qGaN technology looks very promising for future power electronics and we can't wait to work with them. **This innovation can bring several benefits to customers in different applications by addressing energy efficiency and power quality in a compact form factor.** QPT's solution is effectively addressing some of the key challenges with the qGaN technology, and this can truly challenge SiC in the future."

Harri Mustonen, Head of Strategy & Business Development



### **Benefit**

- Faster switching = lower losses
  - Improve VFD efficiency 5-10%
  - Less heat
  - Improved reliability
- Integrated filter = Clean sine into motor
  - Further efficiency saving: another 5+%
  - Reduced eddy currents & winding losses
  - · Less strain on motor, improved reliability
  - Reduces noise & vibration
  - No common mode or dc path
- Eliminates EMI/RFI: No need for screened cables
- Dramatically higher power density, smaller lighter VFD / motor systems
  - Enables novel motor designs & integrated VFD

### Environmental impact: Equivalent to removing 50% of the planes from the sky



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### Summary

- Electric motors consume ~50% of world electricity, rising quickly with electrification But much of this is shockingly wasteful
- Net zero compelling need to make electric motors more efficient
- GaN is *inherently* a better transistor than Si or SiC: faster, no body diode, lower capacitance
- But it has been hard to use...
- GaN for Power electronics has been limited to low power, soft switching (eg "wall-wart" PSU)
- But good system design allows GaN to be used in higher power & hardswitching
- QPT + Infineon: unleashing the power of GaN to make electric motors radically better
- Save \$66bn in energy, 400m tonnes of CO2





# THANK YOU

**COMPANY OVERVIEW** 

2024

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